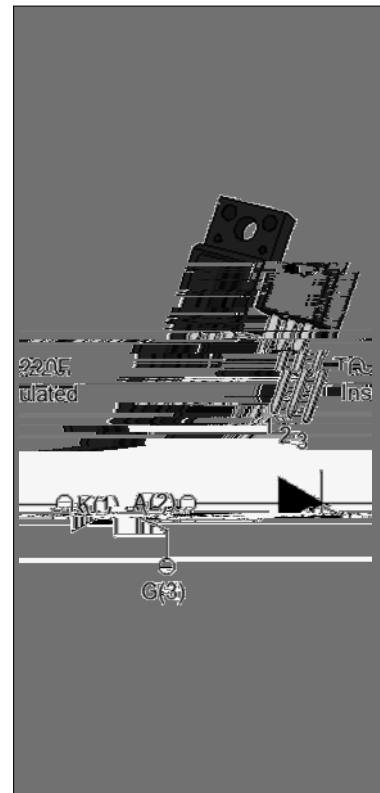




With high ability to withstand the shock loading of large current, JCT812F of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT812F provides a rated insulation voltage of 2000 V_{RMS} , complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	15	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
Average on-state current ($T_c=86^\circ C$)	$I_{T(AV)}$	7.6	A
RMS on-state current ($T_c=86^\circ C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	140	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		154	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	98	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	150	$A/\mu s$



Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	60	mA
I_H	$I_T=500mA$	-	-	50	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$	500	-	-	V/ μs
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$	-	5	-	μs

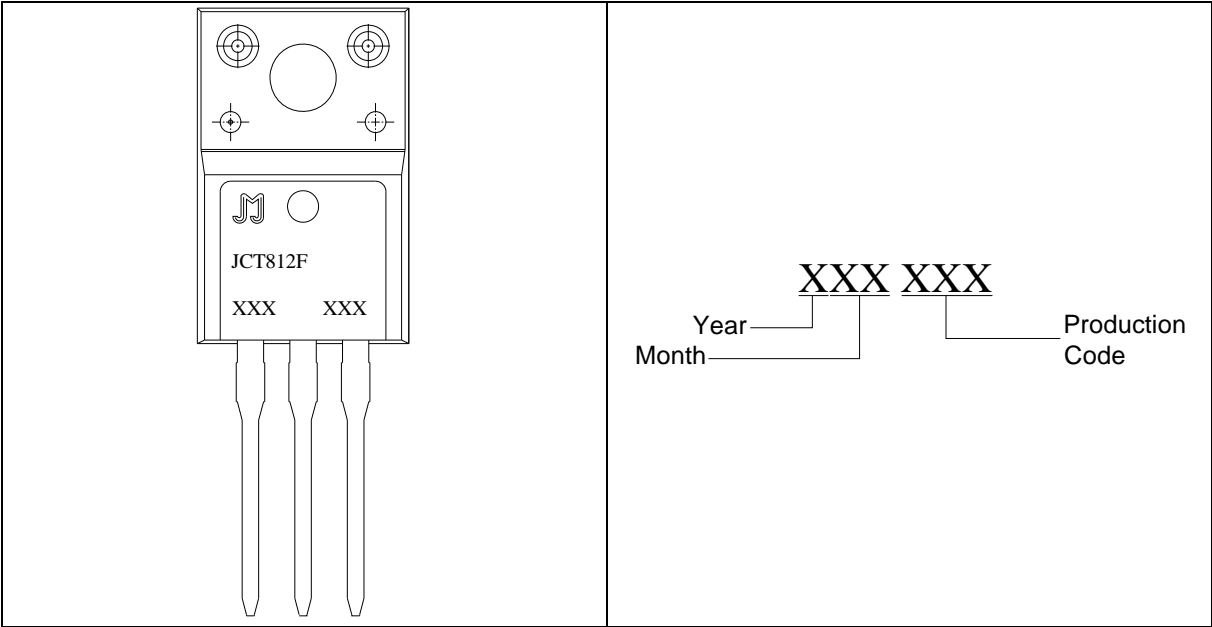
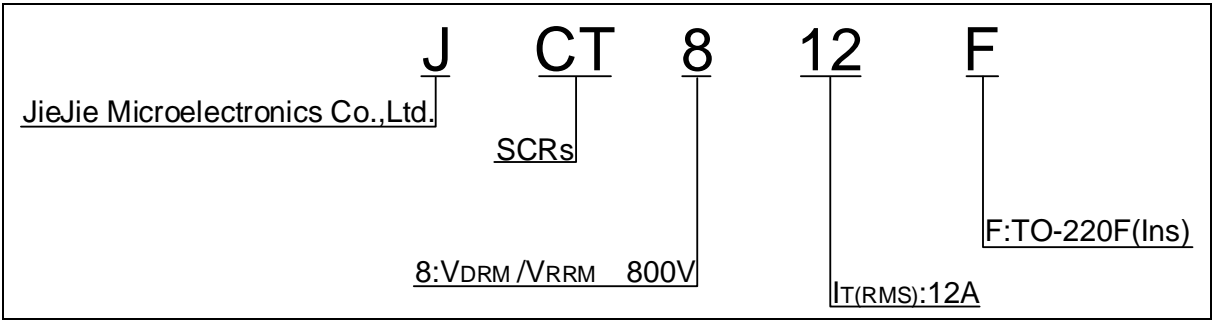
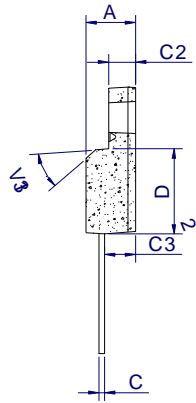
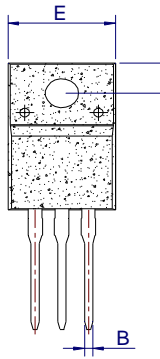
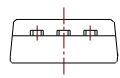





FIG.1: Maximum power dissipation versus
M



A

M

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